

Transistors with Built-in Resistor DRC2514E0L

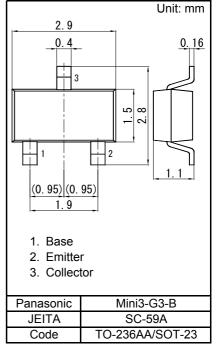
DRC2514E0L Silicon NPN epitaxial planar type

For digital circuits Complementary to DRA2514E

Features

- Low collector-emitter saturation voltage Vce(sat)
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)
- Marking Symbol: V6
- Packaging

Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)



V V	Internal	Con	nectior	า
πA				
nW	R ₁	. 」	OC	
°C	B ∽−Ė−	t K		
°C	R ₂		0 F	
°C		•	oE	
	Resistance	R1	10	kΩ
	value	R2	10	kΩ

Absolute Maximum Ra	atings Ta = 25 ℃

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	VCBO	50	V
Collector-emitter voltage (Base open)	VCEO	50	V
Collector current	IC	500	mA
Total power dissipation	PT	200	mW
Junction temperature	Tj	150	С°
Operating ambient temperature	Topr	-40 to +85	С°
Storage temperature	Tstg	-55 to +150	°C

Electrical Characteristics	5 Ta = 25 °C ± 3 °C
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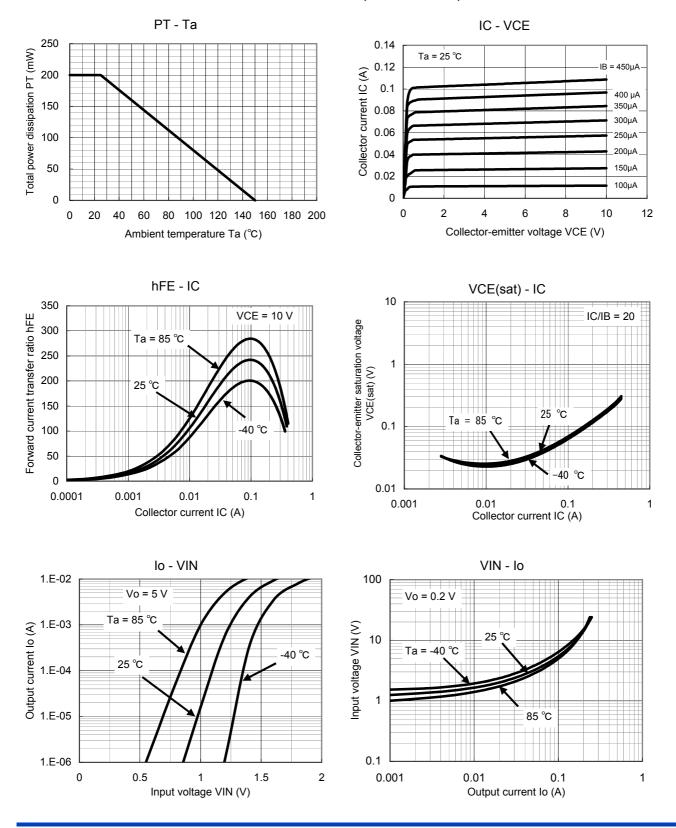
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	VCBO	IC = 10 μA, IE = 0	50			V
Collector-emitter voltage (Base open)	VCEO	IC = 2 mA, IB = 0	50			V
Collector-base cutoff current (Emitter open)	ICBO	VCB = 50 V, IE = 0			1	μA
Collector-emitter cutoff current (Base open)	ICEO	VCE = 50 V, IB = 0			1	μA
Emitter-base cutoff current (Collector open)	IEBO	VEB = 6 V, IC = 0			1	mA
Forward current transfer ratio	hFE	VCE = 10 V, IC = 100 mA	60			-
Collector-emitter saturation voltage	VCE(sat)	IC = 100 mA, IB = 5 mA			0.25	V
Input voltago	Vi(on)	VCE = 0.2 V, IC = 50 mA	5.7			V
Input voltage	Vi(off)	VCE = 5 V, IC = 100 µA			0.7	V
Input resistance	R1		-30%	10	+30%	kΩ
Resistance ratio	R1/R2		0.8	1.0	1.2	-

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

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Technical Data (reference)



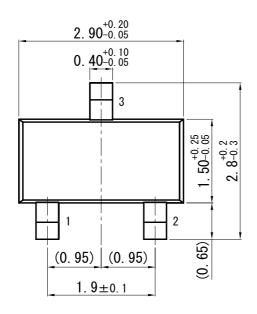
Established : 2010-01-29 Revised : 2014-03-07 Doc No. TT4-EA-12295 Revision. 2

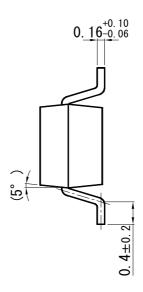


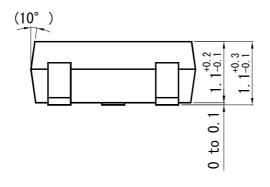
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Mini3-G3-B

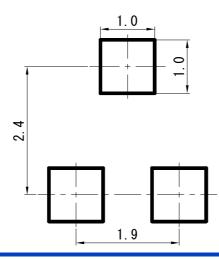
Unit: mm







Land Pattern (Reference) (Unit: mm)



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Established : 2010-01-29 Revised : 2014-03-07

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